

HAF2001

Silicon N Channel MOS FET Series Power Switching

REJ03G1134-0700
(Previous: ADE-208-353D)
Rev.7.00
Apr 27, 2006

Description

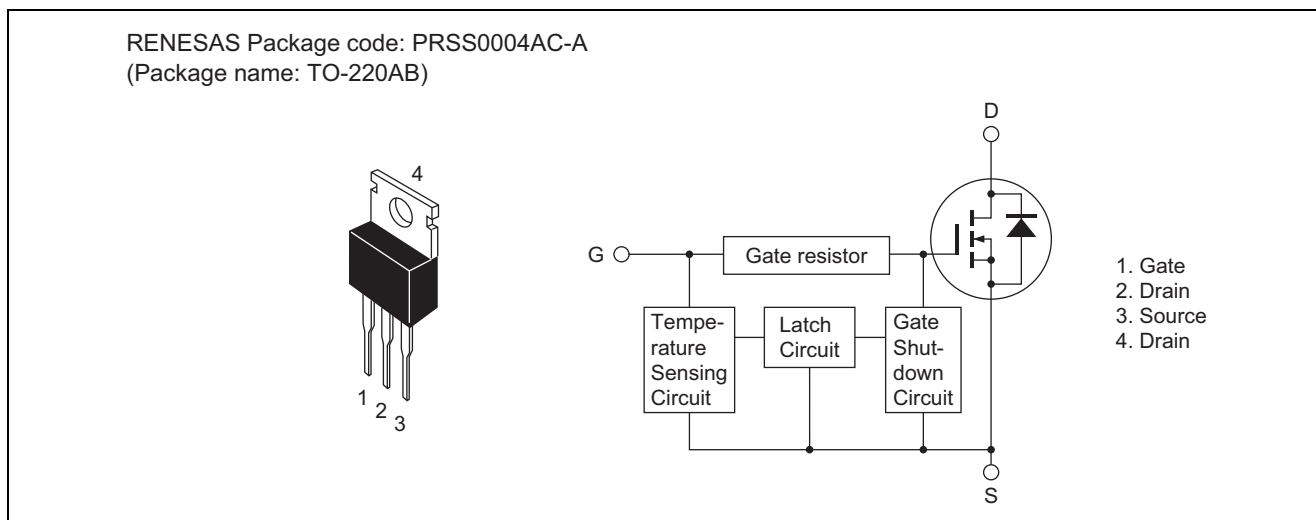
This FET has the over temperature shut-down capability sensing to the junction temperature.

This FET has the built-in over temperature shut-down circuit in the gate area. And this circuit operation to shut-down the gate voltage in case of high junction temperature like applying over power consumption, over current etc.

Features

- Logic level operation (4 to 6 V Gate drive)
- High endurance capability against to the short circuit
- Built-in the over temperature shut-down circuit
- Latch type shut-down operation (Need 0 voltage recovery)

Outline



Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Drain to source voltage	V _{DSS}	60	V
Gate to source voltage	V _{GSS}	16	V
	V _{GSS}	-2.8	V
Drain current	I _D	20	A
Drain peak current	I _{D (pulse)} ^{Note 1}	40	A
Body-drain diode reverse drain current	I _{DR}	20	A
Channel dissipation	P _{ch} ^{Note 2}	50	W
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1%

2. Value at Ta = 25°C

Typical Operation Characteristics

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Input voltage	V _{IH}	3.5	—	—	V	
	V _{IL}	—	—	1.2	V	
Input current (Gate non shut down)	I _{IH1}	—	—	100	μA	V _i = 8 V, V _{DS} = 0
	I _{IH2}	—	—	50	μA	V _i = 3.5 V, V _{DS} = 0
	I _{IL}	—	—	1	μA	V _i = 1.2 V, V _{DS} = 0
Input current (Gate shut down)	I _{IH (sd) 1}	—	0.8	—	mA	V _i = 8 V, V _{DS} = 0
	I _{IH (sd) 2}	—	0.35	—	mA	V _i = 3.5 V, V _{DS} = 0
Shut down temperature	T _{sd}	—	175	—	°C	Channel temperature
Gate operation voltage	V _{OP}	3.5	—	13	V	

Electrical Characteristics

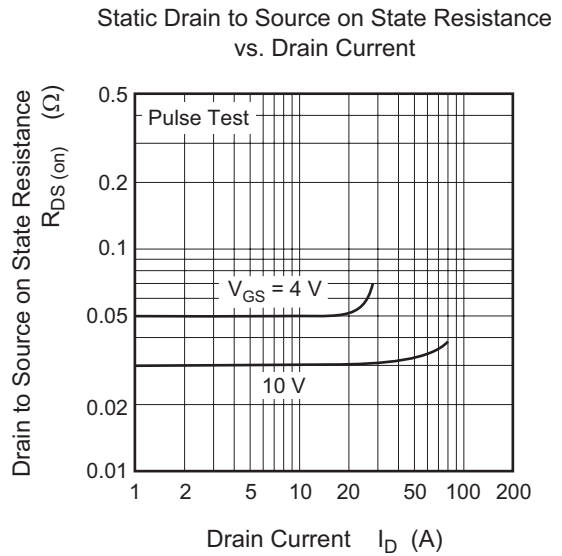
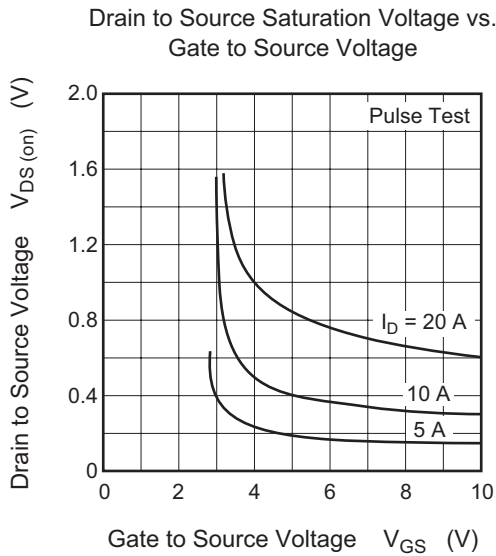
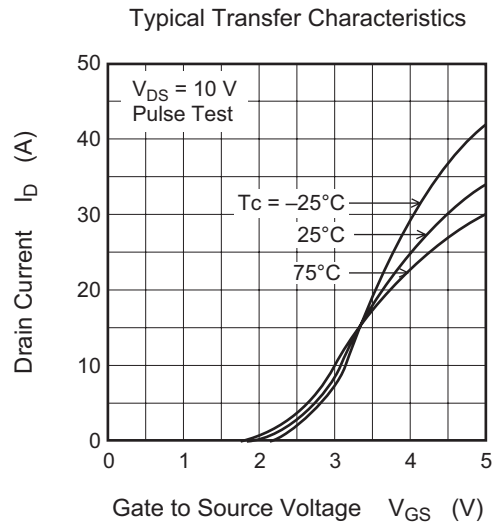
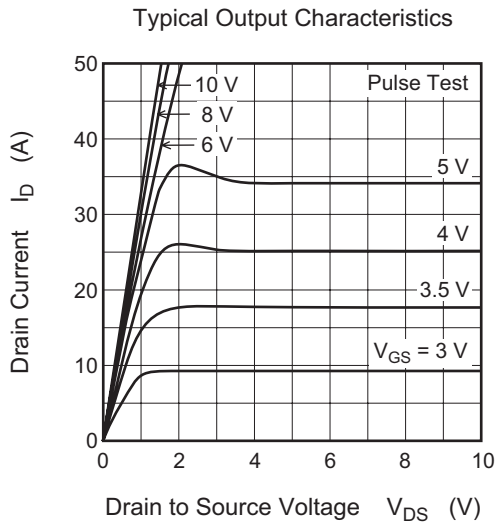
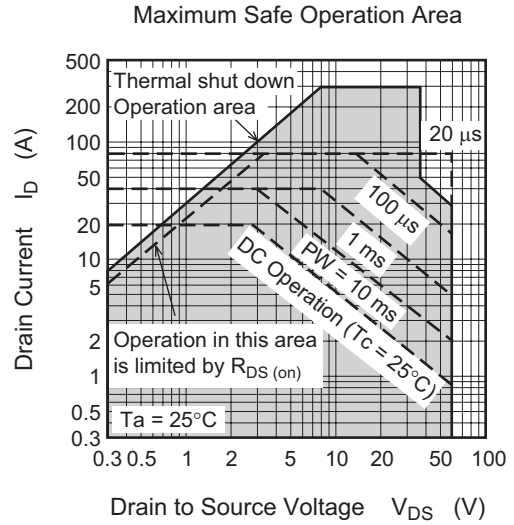
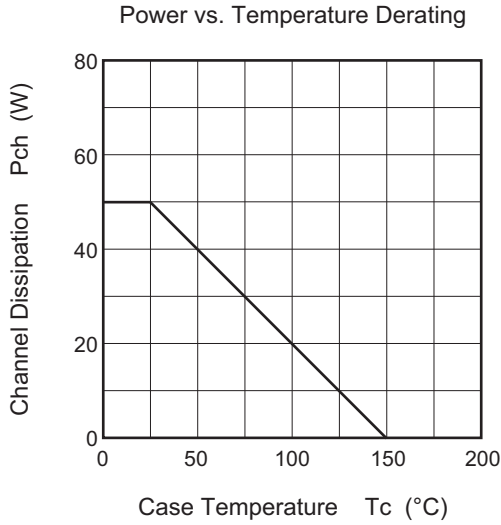
(Ta = 25°C)

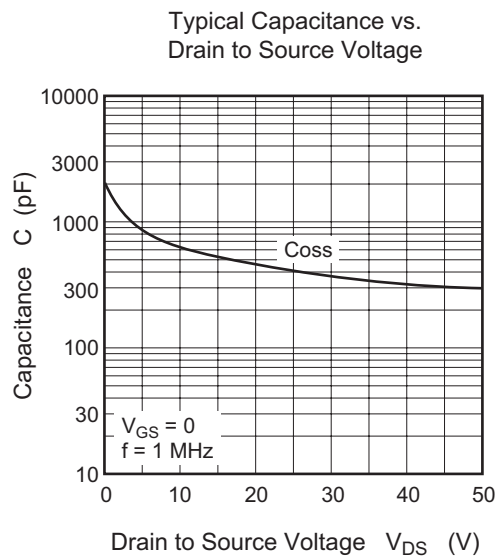
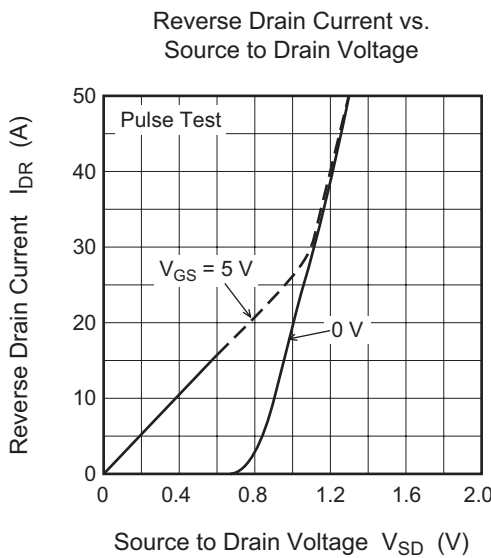
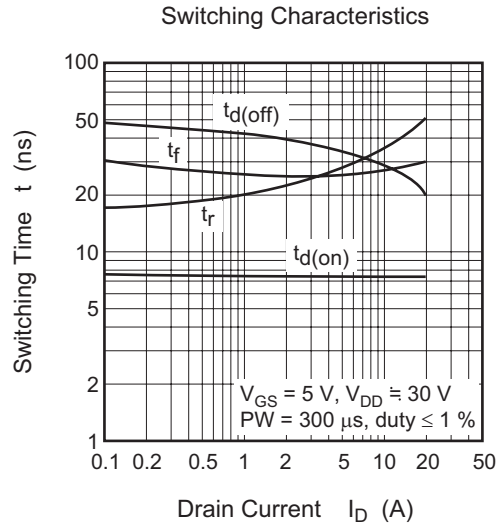
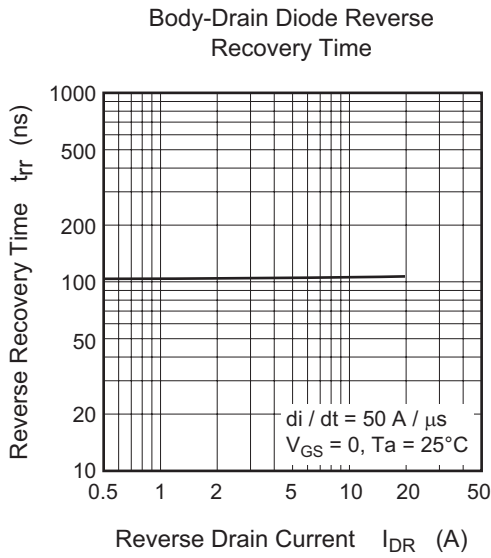
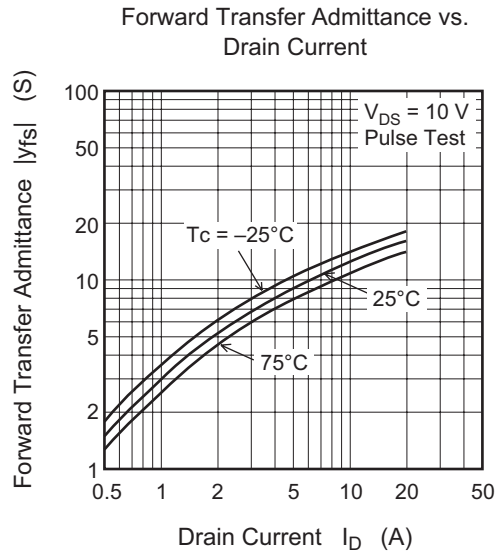
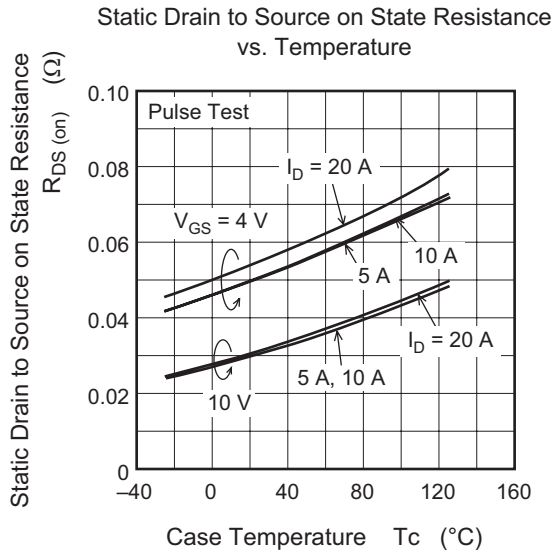
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain current	I_{D1}	10	—	—	A	$V_{GS} = 3.5 \text{ V}, V_{DS} = 2 \text{ V}$
	I_{D2}	—	—	10	mA	$V_{GS} = 1.2 \text{ V}, V_{DS} = 2 \text{ V}$
Drain to source breakdown voltage	$V_{(BR)DSS}$	60	—	—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	16	—	—	V	$I_G = 100 \mu\text{A}, V_{DS} = 0$
	$V_{(BR)GSS}$	-2.8	—	—	V	$I_G = -100 \mu\text{A}, V_{DS} = 0$
Gate to source leak current	I_{GSS1}	—	—	100	μA	$V_{GS} = 8 \text{ V}, V_{DS} = 0$
	I_{GSS2}	—	—	50	μA	$V_{GS} = 3.5 \text{ V}, V_{DS} = 0$
	I_{GSS3}	—	—	1	μA	$V_{GS} = 1.2 \text{ V}, V_{DS} = 0$
	I_{GSS4}	—	—	-100	μA	$V_{GS} = -2.4 \text{ V}, V_{DS} = 0$
Input current (shut down)	$I_{GS(op)1}$	—	0.8	—	mA	$V_{GS} = 8 \text{ V}, V_{DS} = 0$
	$I_{GS(op)2}$	—	0.35	—	mA	$V_{GS} = 3.5 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	250	μA	$V_{DS} = 50 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	—	2.25	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	50	65	m Ω	$I_D = 10 \text{ A}, V_{GS} = 4 \text{ V}$ ^{Note 3}
	$R_{DS(on)}$	—	30	43	m Ω	$I_D = 10 \text{ A}, V_{GS} = 10 \text{ V}$ ^{Note 3}
Forward transfer admittance	$ y_{fs} $	6	12	—	S	$I_D = 10 \text{ A}, V_{DS} = 10 \text{ V}$ ^{Note 3}
Output capacitance	C_{oss}	—	630	—	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0$ $f = 1 \text{ MHz}$
Turn-on delay time	$t_{d(on)}$	—	7.5	—	μs	$I_D = 5 \text{ A}$ $V_{GS} = 5 \text{ V}$ $R_L = 6 \Omega$
Rise time	t_r	—	29	—	μs	
Turn-off delay time	$t_{d(off)}$	—	34	—	μs	
Fall time	t_f	—	26	—	μs	
Body-drain diode forward voltage	V_{DF}	—	1.0	—	V	$I_F = 20 \text{ A}, V_{GS} = 0$
Body-drain diode reverse recovery time	t_{rr}	—	110	—	ns	$I_F = 20 \text{ A}, V_{GS} = 0$ $di_F/dt = 50 \text{ A}/\mu\text{s}$
Over load shut down operation time ^{Note4}	t_{os1}	—	1.8	—	ms	$V_{GS} = 5 \text{ V}, V_{DD} = 12 \text{ V}$
	t_{os2}	—	0.7	—	ms	$V_{GS} = 5 \text{ V}, V_{DD} = 24 \text{ V}$

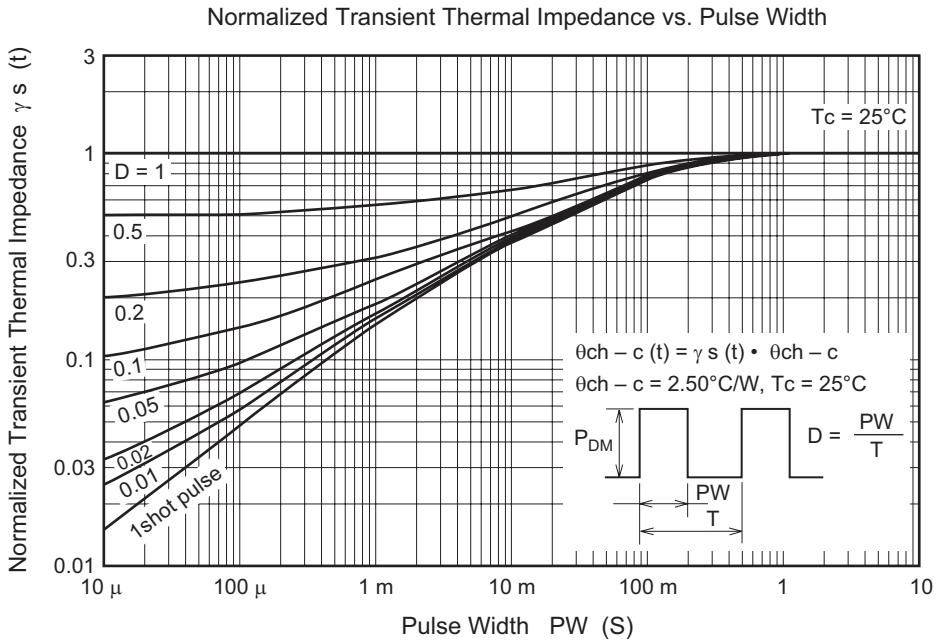
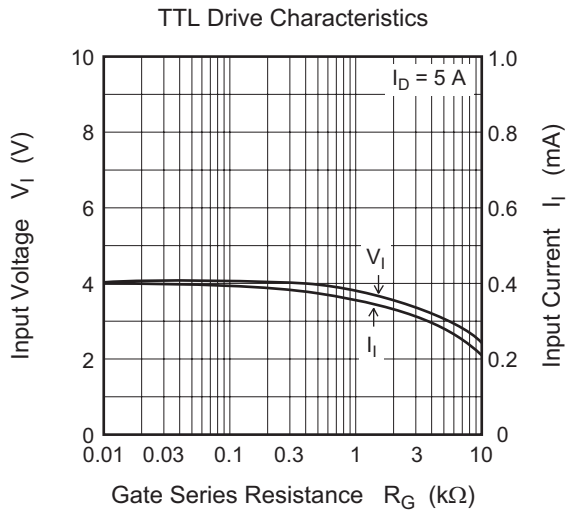
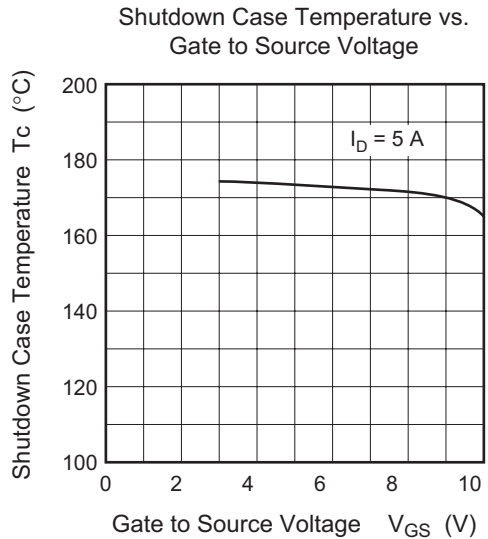
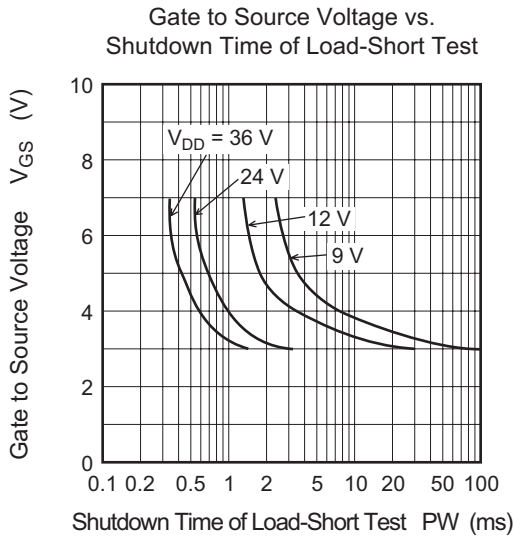
Notes: 3. Pulse test

4. Include the time shift based on increasing of channel temperature when operate under over load condition.

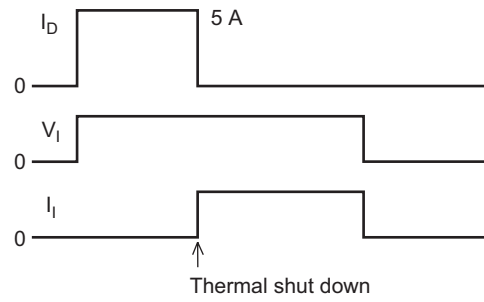
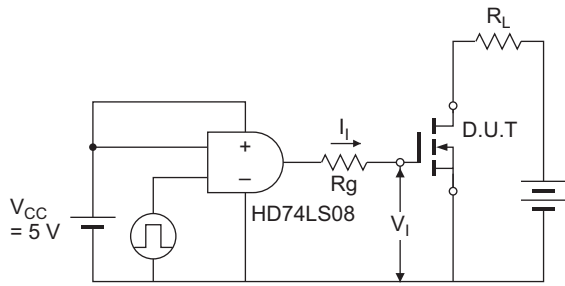
Main Characteristics



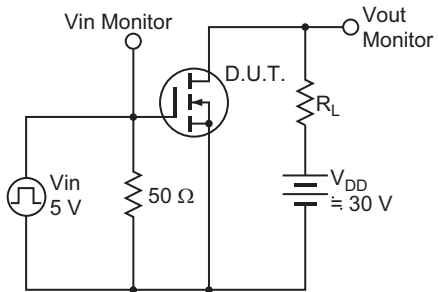




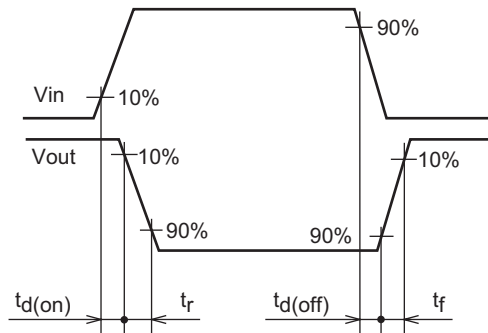
Test Circuit



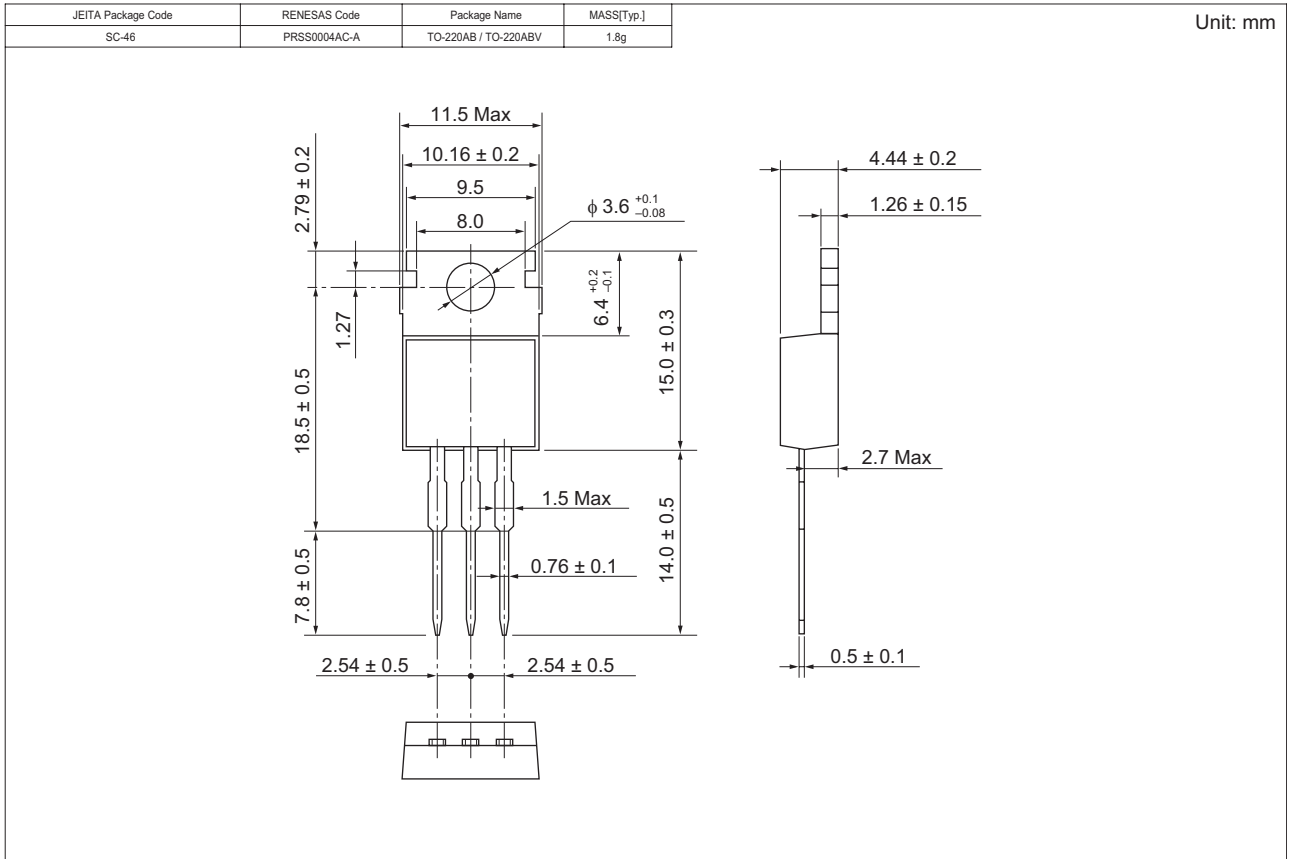
Switching Time Test Circuit



Waveform



Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
HAF2001-90	Max: 50 pcs/sack	Sack

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